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(to be used for all correspondence after initial filing)

Application Number	09/352,362
Filing Date	July 13, 1999
First Named Inventor	Shunpei YAMAZAKI et al.
Group Art Unit	2815
Examiner Name	J. Diaz
Attorney Docket Number	0756-1996
Total Number of Pages in This Submission	

**ENCLOSURES (check all that apply)**

<input type="checkbox"/> Fee Transmittal Form <input checked="" type="checkbox"/> Fee Attached <input checked="" type="checkbox"/> Amendment / Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input checked="" type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input checked="" type="checkbox"/> Information Disclosure Statement <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers (for an Application) <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Declaration and Power of Attorney <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s) _____	<input type="checkbox"/> After Allowance Communication to Group <input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences <input type="checkbox"/> Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) <input type="checkbox"/> Proprietary Information <input type="checkbox"/> Status Letter <input checked="" type="checkbox"/> Other Enclosures 1. Change of Correspondence Address Form 2. 3. 4. 5. 6.
Remarks		<input checked="" type="checkbox"/> The Commissioner is hereby authorized to charge any additional fees required or credit any overpayments to Deposit Account No. 50-2280 for the above identified docket number.

**SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT**

Firm or Individual name	Eric J. Robinson, Reg. No. 38,285 Robinson Intellectual Property Law Office, P.C. PMB 955 21010 Southbank Street Potomac Falls, VA 20165
Signature	
Date	9-20-02

**CERTIFICATE OF MAILING**

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Type or printed name	Ava M. Dixon		
Signature		Date	9/20/02

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Inter Patent Application of

Shunpei YAMAZAKI et al.

Serial No. 09/352,362

Filed: July 13, 1999

For: CRYSTALLINE SEMICONDUCTOR

THIN FILM, METHOD OF FABRICATING

THE SAME, SEMICONDUCTOR DEVICE,

AND METHOD OF FABRICATING THE

SAME

) Art Unit: 2815

) Examiner: J. Diaz

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**AMENDMENT**

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

In response to the Office Action dated April 25, 2002 please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please cancel claims 25, 26 and 116-122 and amend claims 15, 17, 20, 22, 28 and 30-35 as follows:

15. (Amended) A method of fabricating a semiconductor device comprising:  
adding an element for facilitating crystallization of an amorphous  
semiconductor thin film to a part or an entire region of the amorphous semiconductor thin  
film;

carrying out a first heat treatment to transform the part or the entire region of  
the amorphous semiconductor thin film into a crystalline semiconductor thin film;

irradiating a laser light to said crystalline semiconductor thin film; and

carrying out a second heat treatment for the crystalline semiconductor thin  
film at 900 to 1200 °C in a reducing atmosphere after the irradiation of said laser light,

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